

Vishay Siliconix

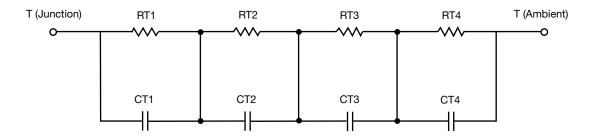
## **R-C Thermal Model Parameters**

## DESCRIPTION

The parametric values in the R-C thermal model have been derived using curve-fitting techniques. R-C values for the electrical circuit in the Foster/tank and Cauer/filter configurations are included. When implemented in PSpice, these values have matching characteristic curves to the single-pulse transient thermal impedance curves for the MOSFET.

These RC values can be used in the PSpice simulation to evaluate the thermal behavior of the MOSFET junction temperature under a defined power profile. These techniques are described in application note AN609, "Thermal Simulation of Power MOSFETs on the PSpice Platform".

## **R-C THERMAL MODEL FOR TANK CONFIGURATION**



R-C VALUES FOR TANK CONFIGURATION THERMAL RESISTANCE (°C/W)					
RT1	n/a	112.2723m	n/a		
RT2	n/a	236.1522m	n/a		
RT3	n/a	575.1598m	n/a		
RT4	n/a	28.9012m	n/a		
·	THERMAL CAPAC	ITANCE (Joules/°C)			
Junction to	Ambient	Case	Foot		
CT1	n/a	6.8072m	n/a		
CT2	n/a	12.5372m	n/a		
CT3	n/a	70.2128m	n/a		
CT4	n/a	476.8608u	n/a		

Note

• n/a indicates not applicable

This document is intended as a SPICE modeling guideline and does not constitute a commercial product datasheet. Designers should refer to the appropriate datasheet of the same number for guaranteed specification limits.

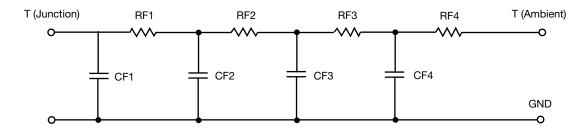
Revision: 28-Oct-2022

1



Vishay Siliconix

## **R-C THERMAL MODEL FOR FILTER CONFIGURATION**



VALUES FOR FILTER CONFIGURATION					
THERMAL RESISTANCE (°C/W)					
Junction to	Ambient	Case	Foot		
RF1	n/a	115.9868m	n/a		
RF2	n/a	320.3595m	n/a		
RF3	n/a	447.5658m	n/a		
RF4	n/a	68.6261m	n/a		
	THERMAL CAPAC	ITANCE (Joules/°C)			
Junction to	Ambient	Case	Foot		
CF1	n/a	1.7833m	n/a		
CF2	n/a	5.6662m	n/a		
CF3	n/a	68.6805m	n/a		
CF4	n/a	1.2345m	n/a		

Note

• n/a indicates not applicable



SiHK125N60EF\_RC

Vishay Siliconix

